

# RFMD



## GaN Foundry Services

### RFMD® GaN Technologies

- 0.5µm gate length HEMT transistor AlGaN/GaN on SiC
- High power density, up to 8W/mm CW
- High breakdown voltage enables;
  - 48V operating voltage CW
  - 65V operating voltage pulsed
- High efficiency >65% achieved for RFMD products
- MTTF > 1 x 10<sup>7</sup> hours at T<sub>channel</sub> = 200°C
- 100Ω/□ thin film resistor and high-resistance epi resistor
- 135pf/mm<sup>2</sup> MIM capacitor with 340V breakdown
- Through wafer vias

### Process Technology Offerings

#### GaN1 - High Power

- Power density – up to 8W/mm
- High breakdown voltage >400V
- Technology developed and manufactured in US

#### GaN2 - High Linearity

- 6dB linearity improvement over GaN1
  - Power density – up to 4W/mm
  - High breakdown voltage >300V
- Technology developed and manufactured in US

#### IPC3 - Integrated Passive Components for High Power

- Passives only, on 6" GaAs wafers
- 3 metal layers for complex interconnections and for high current capability (up to 28mA/µm)
- High breakdown voltage capacitors – up to 340V
- Technology developed and manufactured in US



RFMD® develops and manufactures unmatched compound semiconductor technologies and offers foundry services for our industry-leading 0.5µm GaN on SiC process. Our world-class manufacturing scale, supported by the largest III-V factory in the world, enables best-in-class cycle times backed by our on-time shipment pledge.

For more information on RFMD GaN Foundry Services, contact: [RFMDFoundryServices@rfmd.com](mailto:RFMDFoundryServices@rfmd.com) or visit [www.rfmd.com/foundry](http://www.rfmd.com/foundry)